

Åenol Kaya

List of Publications by Year in descending order

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Version: 2024-02-01

30
papers

554
citations

567281

15
h-index

642732

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all docs

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docs citations

30
times ranked

392
citing authors

#	ARTICLE	IF	CITATIONS
1	A detailed study on frequency dependent electrical characteristics of MOS capacitors with dysprosium oxide gate dielectrics. <i>Semiconductor Science and Technology</i> , 2020, 35, 025002.	2.0	9
2	Nanostructure, optical and electrical properties of p-NiO/n-Si heterojunction diodes. <i>Applied Physics A: Materials Science and Processing</i> , 2020, 126, 1.	2.3	8
3	Co-60 gamma radiation influences on the electrochemical, physical and electrical characteristics rare-earth dysprosium oxide (Dy2O3). <i>Radiation Physics and Chemistry</i> , 2020, 171, 108684.	2.8	12
4	Influences of platinum doping concentrations and operation temperatures on oxygen sensitivity of Pt/SnO2/Pt resistive gas sensors. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 14813-14821.	2.2	3
5	Effect of annealing temperature on structural, electrical, and UV sensing characteristics of n-ZnO/p-Si heterojunction photodiodes. <i>Turkish Journal of Physics</i> , 2019, 43, 252-263.	1.1	11
6	Effects of interfacial layer on the electrical properties of n-ZnO/p-Si heterojunction diodes between 260 and 340ÅK. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 12170-12179.	2.2	10
7	Co-60 gamma irradiation influences on device characteristics of n-SnO2/p-Si heterojunction diodes. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2019, 445, 63-68.	1.4	11
8	Fabrication and characterization of Si-PIN photodiodes. <i>Turkish Journal of Physics</i> , 2019, 43, 556-562.	1.1	5
9	Evolutions on surface chemistry, microstructure, morphology and electrical characteristics of SnO2/p-Si heterojunction under various annealing parameters. <i>Journal of Alloys and Compounds</i> , 2019, 778, 889-899.	5.5	14
10	Modifications of structural, chemical, and electrical characteristics of Er2O3/Si interface under Co-60 gamma irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2018, 418, 74-79.	1.4	38
11	Co-60 gamma irradiation influences on physical, chemical and electrical characteristics of HfO2/Si thin films. <i>Radiation Physics and Chemistry</i> , 2018, 150, 64-70.	2.8	12
12	Co-60 gamma irradiation effects on electrical characteristics of HfO2 MOSFETs and specification of basic radiation- induced degradation mechanism. <i>Radiation Physics and Chemistry</i> , 2018, 149, 7-13.	2.8	12
13	Effects of annealing temperature on electrical characteristics of sputtered Al/Al2O3/p-Si (MOS) capacitors. <i>Turkish Journal of Physics</i> , 2018, 42, 470-477.	1.1	5
14	Impact of interfacial layer using ultra-thin SiO2 on electrical and structural characteristics of Gd2O3 MOS capacitor. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 17473-17482.	2.2	12
15	The gamma irradiation responses of yttrium oxide capacitors and first assessment usage in radiation sensors. <i>Sensors and Actuators A: Physical</i> , 2017, 258, 44-48.	4.1	13
16	Yttrium oxide nanostructured thin films deposited by radio frequency sputtering: the annealing optimizations and correlations between structural, morphological, optical and electrical properties. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 13920-13927.	2.2	9
17	Evaluation of Radiation Sensor Aspects of Er_2O_3 MOS Capacitors under Zero Gate Bias. <i>IEEE Transactions on Nuclear Science</i> , 2016, 63, 1284-1293.	2.0	34
18	A detailed study on the frequency-dependent electrical characteristics of Al/HfSiO4/p-Si MOS capacitors. <i>Journal of Materials Science: Materials in Electronics</i> , 2016, 27, 13154-13160.	2.2	20

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19	A Detailed Study on Zero-Bias Irradiation Responses of MOS Capacitors. IEEE Transactions on Nuclear Science, 2016, 63, 1301-1305.	2.0	16
20	Samarium oxide thin films deposited by reactive sputtering: Effects of sputtering power and substrate temperature on microstructure, morphology and electrical properties. Materials Science in Semiconductor Processing, 2015, 33, 42-48.	4.0	38
21	A Comprehensive Study on the Frequency-Dependent Electrical Characteristics of Sm ₂ O ₃ MOS Capacitors. IEEE Transactions on Electron Devices, 2015, 62, 980-987.	3.0	40
22	Structural and electrical characterizations of BiFeO ₃ capacitors deposited by sol-gel dip coating technique. Thin Solid Films, 2015, 590, 7-12.	1.8	18
23	Frequency dependent gamma-ray irradiation response of Sm ₂ O ₃ MOS capacitors. Nuclear Instruments & Methods in Physics Research B, 2015, 358, 188-193.	1.4	30
24	Effects of post deposition annealing, interface states and series resistance on electrical characteristics of HfO ₂ MOS capacitors. Journal of Materials Science: Materials in Electronics, 2015, 26, 8277-8284.	2.2	33
25	Characterization of interface defects in BiFeO ₃ metal-oxide-semiconductor capacitors deposited by radio frequency magnetron sputtering. Journal of Materials Science: Materials in Electronics, 2015, 26, 5987-5993.	2.2	15
26	Influences of Co-60 gamma-ray irradiation on electrical characteristics of Al ₂ O ₃ MOS capacitors. Journal of Radioanalytical and Nuclear Chemistry, 2014, 302, 425-431.	1.5	22
27	Use of BiFeO ₃ layer as a dielectric in MOS based radiation sensors fabricated on a Si substrate. Nuclear Instruments & Methods in Physics Research B, 2014, 319, 168-170.	1.4	18
28	Frequency dependent electrical characteristics of BiFeO ₃ MOS capacitors. Journal of Alloys and Compounds, 2014, 583, 476-480.	5.5	43
29	Effects of Substrate Temperature on the Microstructure and Morphology of CdZnTe Thin Films. Journal of Electronic Materials, 2014, 43, 4011-4017.	2.2	23
30	Effects of gamma-ray irradiation on interface states and series-resistance characteristics of BiFeO ₃ MOS capacitors. Nuclear Instruments & Methods in Physics Research B, 2014, 319, 44-47.	1.4	20